

SOT-23 Formed SMD Package

**BCW67, A, B, C
BCW68, F, G, H**

GENERAL PURPOSE TRANSISTOR

P-N-P transistor

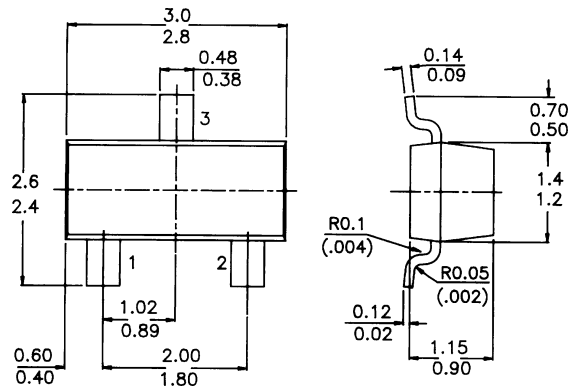
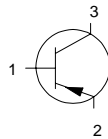
Marking

- BCW67A = DA
- BCW67B = DB
- BCW67C = DC
- BCW68F = DF
- BCW68G = DG
- BCW68H = DH

PACKAGE OUTLINE DETAILS
ALL DIMENSIONS IN mm

Pin configuration

- 1 = BASE
- 2 = EMITTER
- 3 = COLLECTOR



ABSOLUTE MAXIMUM RATINGS

- Collector-base voltage (open emitter) $-V_{CBO}$
- Collector-emitter voltage (open base) $-V_{CEO}$
- Emitter-base voltage (open collector) $-V_{EBO}$
- Collector current (d.c.) $-I_C$
- Total power dissipation at $T_{amb} = 25^\circ C$ P_{tot}
- D.C. current gain

$I_C = 10 \text{ mA}; V_{CE} = 1 \text{ V}$

BCW67A, 68F

BCW67B, 68G

BCW67C, 68H

$I_C = 100 \text{ mA}; V_{CE} = 1 \text{ V}$

BCW67A, 68F

BCW67B, 68G

	BCW 67series	68 series
$-V_{CBO}$	max. 45	60 V
$-V_{CEO}$	max. 32	45 V
$-V_{EBO}$	max. 5	V
$-I_C$	max. 800	mA
P_{tot}	max. 225	mW
h_{FE}	min. 75	
h_{FE}	min. 120	
h_{FE}	min. 180	
h_{FE}	min. 100	
h_{FE}	max. 250	
h_{FE}	min. 160	
h_{FE}	max. 400	

BCW67, A, B, C
BCW68, F, G, H

BCW67C, 68H	h_{FE}	min.	250	
		max.	630	
$I_C = 300 \text{ mA}; V_{CE} = 1 \text{ V}$				
BCW67A, 68F	h_{FE}	min.	35	
BCW67B, 68G	h_{FE}	min.	60	
BCW67C, 68H	h_{FE}	min.	100	
RATINGS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)				
<i>Limiting values</i>				
Collector-base voltage (open emitter)	$-V_{CBO}$	max.	45	60 V
Collector-emitter voltage (open base)	$-V_{CEO}$	max.	32	45 V
Emitter-base voltage (open collector)	$-V_{EBO}$	max.	5	V
Collector current (d.c.)	$-I_C$	max.	800	mA
Total power dissipation at $T_{amb} = 25^\circ\text{C}$	P_{tot}	max	225	mW
Storage temperature	T_{stg}		-55 to +150	$^\circ\text{C}$
THERMAL CHARACTERISTICS				
$T_j = P (R_{th\ j-t} + R_{th\ s-a}) + T_{amb}$				
<i>Thermal resistance</i>				
from junction to ambient	$R_{th\ j-a}$	556	556	556 $^\circ\text{C/mW}$
CHARACTERISTICS (at $T_A = 25^\circ\text{C}$ unless otherwise specified)				
Collector-emitter breakdown voltage			BCW67 series	68 series
$I_C = 10 \text{ mA}; I_B = 0$	$V_{(BR)CEO}$	min.	32	45 V
$I_C = 10 \text{ mA}; V_{EB} = 0$	$V_{(BR)CES}$	min.	45	60 V
Emitter-base breakdown voltage				
$I_E = 10 \text{ mA}; I_C = 0$	$V_{(BR)EBO}$	min.	5	V
Collector cut-off current				
$V_{CE} = 32 \text{ V}; I_E = 0 \text{ V}$	I_{CES}	max.	20	nA
$V_{CE} = 45 \text{ V}; I_E = 0 \text{ V}$	I_{CES}	max.	-	20 nA
$V_{CE} = 32 \text{ V}; I_E = 0 \text{ V}; T_A = 150^\circ\text{C}$	I_{CES}	max.	10	mA
$V_{CE} = 45 \text{ V}; I_E = 0 \text{ V}; T_A = 150^\circ\text{C}$	I_{CES}	max.	-	10 mA
Emitter cut-off current				
$V_{EB} = 4 \text{ V}; I_C = 0$	I_{EBO}	max.	20	nA
Output capacitance at $f = 1 \text{ MHz}$				
$I_E = 0; V_{CB} = 10 \text{ V}$	C_c	max.	18	pF
Input capacitance at $f = 1 \text{ MHz}$				
$I_C = 0; V_{EB} = 0.5 \text{ V}$	C_e	max.	105	pF
Saturation voltages				
$I_C = 300 \text{ mA}; I_B = 30 \text{ mA}$	V_{CEsat}	max.	1.5	V
$I_C = 500 \text{ mA}; I_B = 50 \text{ mA}$	$-V_{BEsat}$	max.	2	V
Noise figure at $R_S = 1 \text{ kW}$				
$I_C = 0.2 \text{ mA}; V_{CE} = 5 \text{ V}$ $f = 1 \text{ KHz}, BW = 200 \text{ Hz}$	NF	max.	10	dB
Transition frequency at $f = 100 \text{ MHz}$				
$I_C = 20 \text{ mA}; V_{CE} = 10 \text{ V}$	f_T	min.	100	MHz

Disclaimer

The product information and the selection guides facilitate selection of the CDIL's Discrete Semiconductor Device(s) best suited for application in your product(s) as per your requirement. It is recommended that you completely review our Data Sheet(s) so as to confirm that the Device(s) meet functionality parameters for your application. The information furnished on the CDIL Web Site/ CD is believed to be accurate and reliable. CDIL however, does not assume responsibility for inaccuracies or incomplete information. Furthermore, CDIL does not assume liability whatsoever, arising out of the application or use of any CDIL product; neither does it convey any license under its patent rights nor rights of others. These products are not designed for use in life saving/support appliances or systems. CDIL customers selling these products (either as individual Discrete Semiconductor Devices or incorporated in their end products), in any life saving/support appliances or systems or applications do so at their own risk and CDIL will not be responsible for any damages resulting from such sale(s).

CDIL strives for continuous improvement and reserves the right to change the specifications of its products without prior notice.



CDIL is a registered Trademark of
Continental Device India Limited

C-120 Naraina Industrial Area, New Delhi 110 028, India.
Telephone + 91-11-579 6150 Fax + 91-11-579 9569, 579 5290
e-mail sales@cdil.com www.cdil.com